NTD5406N, STD5406N

Power MOSFET
40 V, 70 A, Single N−Channel, DPAK

Features
- Low $R_{DS(on)}$
- High Current Capability
- Low Gate Charge
- STD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free and are RoHS Compliant

Applications
- Electronic Brake Systems
- Electronic Power Steering
- Bridge Circuits

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	40	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current − $R_{\theta JC}$	Steady State	T_C = 25°C	I_D	70	A
		T_C = 125°C		40	
Power Dissipation − $R_{\theta JC}$	Steady State	T_C = 25°C	P_D	100	W
Continuous Drain Current − $R_{\theta JA}$ (Note 1)	Steady State	T_A = 25°C	I_D	12.2	A
		T_A = 125°C		7.0	
Power Dissipation − $R_{\theta JA}$ (Note 1)	Steady State	T_A = 25°C	P_D	3.0	W
Pulsed Drain Current	t_p = 10 μs		I_{DM}	150	A
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 175	°C
Source Current (Body Diode) Pulsed			I_S	63.5	A
Single Pulse Drain−to Source Avalanche Energy − (V_{DD} = 50 V, V_{GS} = 10 V, I_{PK} = 30 A, L = 1 mH, R_G = 25 Ω)			EAS	450	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS (Note 1)

Parameter	Symbol	Max	Unit
Junction−to−Case (Drain)	$R_{\theta JC}$	1.5	°C/W
Junction−to−Ambient (Note 1)	$R_{\theta JA}$	49	

1. Surface mounted on FR4 board using 1 sq in pad size, (Cu Area 1.127 sq in [2 oz] including traces).

ON Semiconductor®

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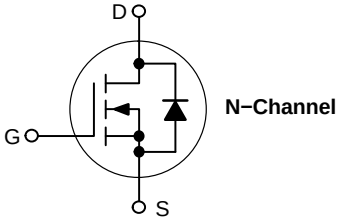
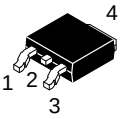
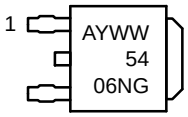
$V_{(BR)DSS}$	$R_{DS(ON)}$ TYP	I_D MAX (Note 1)
40 V	8.7 mΩ @ 10 V	70 A





DPAK
CASE 369C
STYLE 2

MARKING DIAGRAM



A = Assembly Location*
Y = Year
WW = Work Week
5406N = Specific Device Code
G = Pb−Free Device

* The Assembly Location code (A) is front side optional. In cases where the Assembly Location is stamped in the package, the front side assembly code may be blank.

ORDERING INFORMATION

Device	Package	Shipping†
NTD5406NT4G	DPAK (Pb−Free)	2500 / Tape & Reel
STD5406NT4G*	DPAK (Pb−Free)	2500 / Tape & Reel
STD5406NT4G−VF01	DPAK (Pb−Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		40			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$				42		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 40 V	T_J = 25°C			1.0	μA
			T_J = 100°C			10	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±30 V				±100	nA
ON CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		1.5		3.5	V
Gate Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				−7.0		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 30 A			8.7	10	mΩ
		V_{GS} = 5.0 V, I_D = 10 A			13.2	17	
Forward Transconductance	g_{FS}	V_{GS} = 10 V, I_D = 10 A			19		S
CHARGES AND CAPACITANCES							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = 32 V			1375	2500	pF
Output Capacitance	C_{OSS}				370	700	
Reverse Transfer Capacitance	C_{RSS}				160	300	
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 32 V, I_D = 30 A			45		nC
Threshold Gate Charge	$Q_{G(TH)}$				2.0		
Gate−to−Source Charge	Q_{GS}				5.4		
Gate−to−Drain Charge	Q_{GD}				20		
SWITCHING CHARACTERISTICS, V_{GS} = 10 V (Note 3)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 10 V, V_{DD} = 32 V, I_D = 30 A, R_G = 2.5 Ω			7.2		ns
Rise Time	t_r				57		
Turn−Off Delay Time	$t_{d(OFF)}$				30		
Fall Time	t_f				67		
SWITCHING CHARACTERISTICS, V_{GS} = 5 V (Note 3)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 5.0 V, V_{DD} = 20 V, I_D = 30 A, R_G = 2.5 Ω			15		ns
Rise Time	t_r				147		
Turn−Off Delay Time	$t_{d(OFF)}$				20		
Fall Time	t_f				29		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 10 A	T_J = 25°C		0.82	1.1	V
			T_J = 125°C		0.67		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dI_{SD}/dt = 100 A/μs, I_S = 10 A			46		ns
Charge Time	t_a				24		
Discharge Time	t_b				22		
Reverse Recovery Charge	Q_{RR}				65		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
3. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

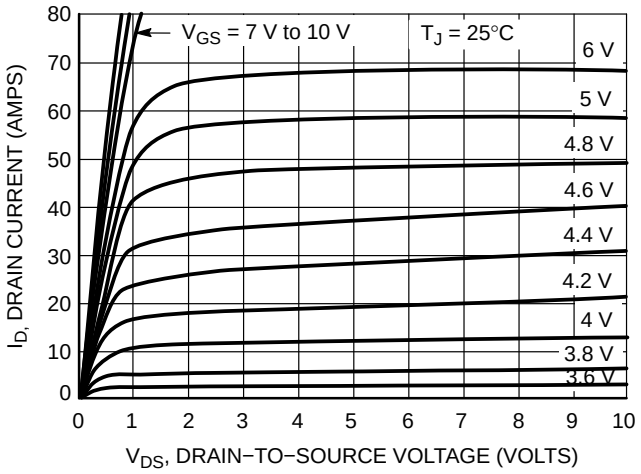


Figure 1. On−Region Characteristics

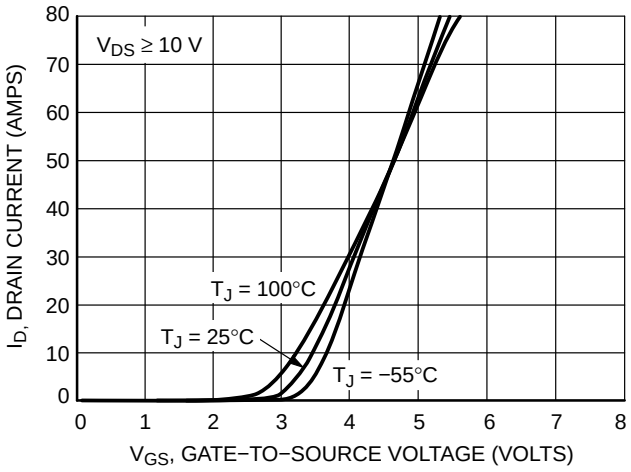


Figure 2. Transfer Characteristics

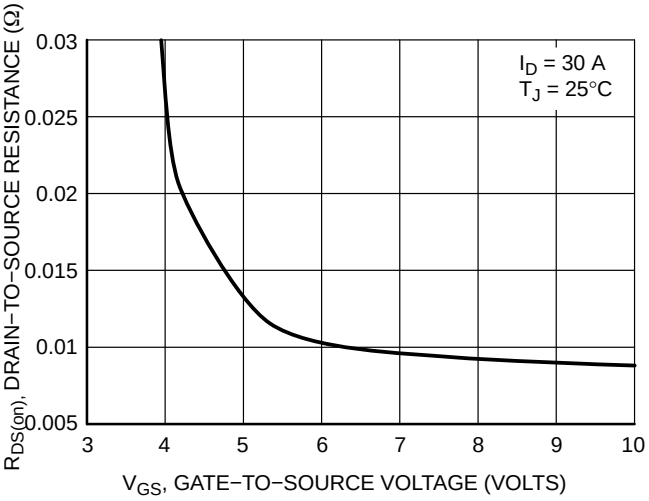


Figure 3. On−Resistance vs. Gate−to−Source Voltage

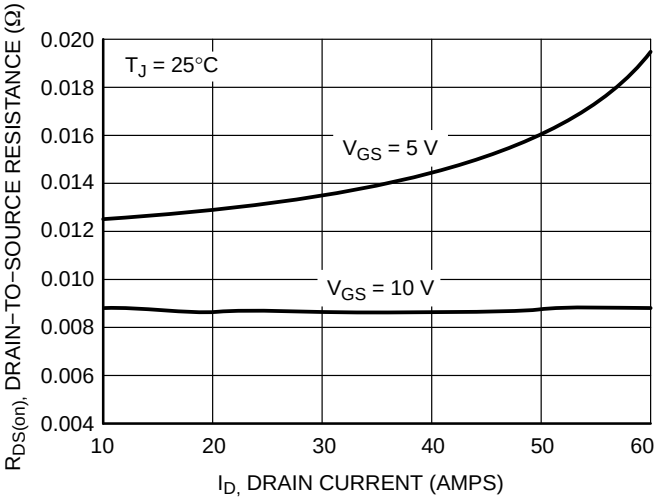


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

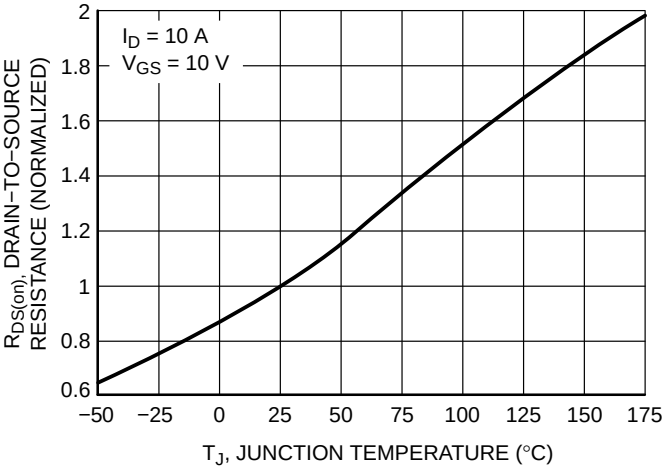


Figure 5. On−Resistance Variation with Temperature

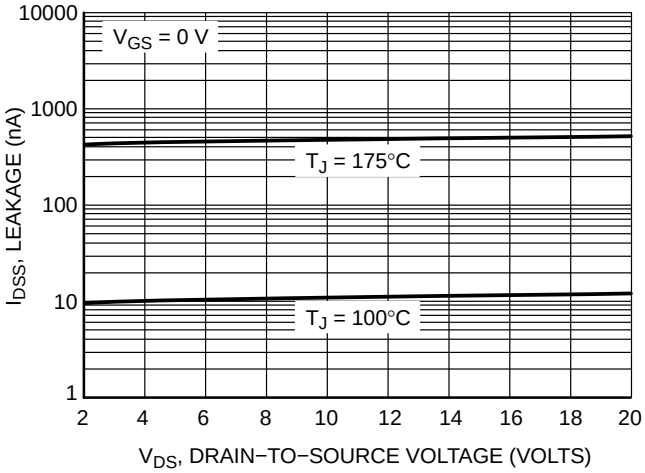


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES

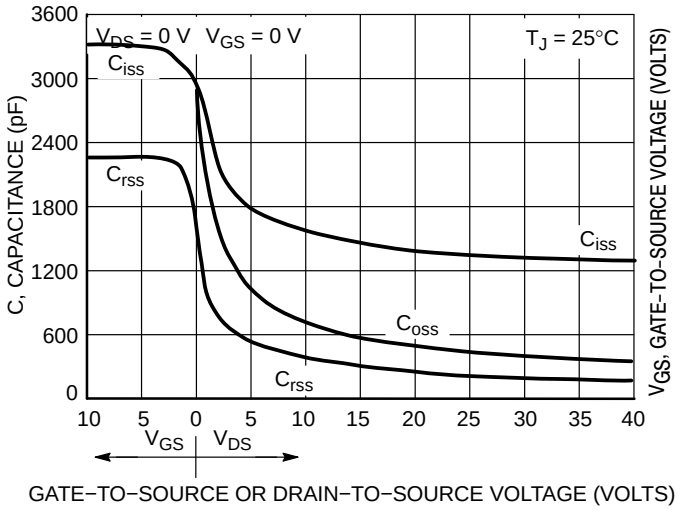


Figure 7. Capacitance Variation

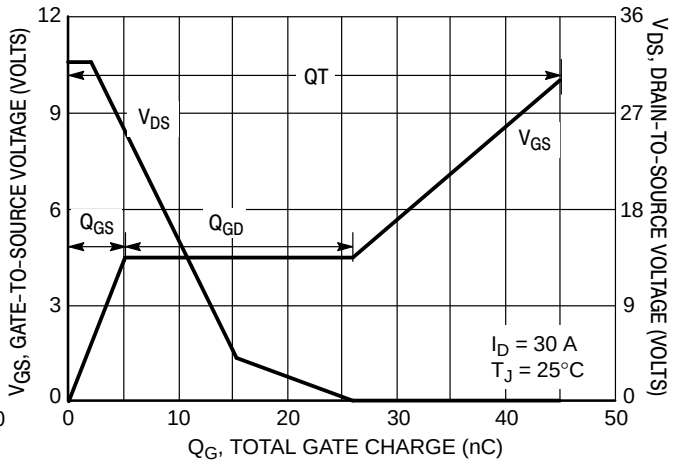


Figure 8. Gate−To−Source and Drain−To−Source Voltage vs. Total Charge

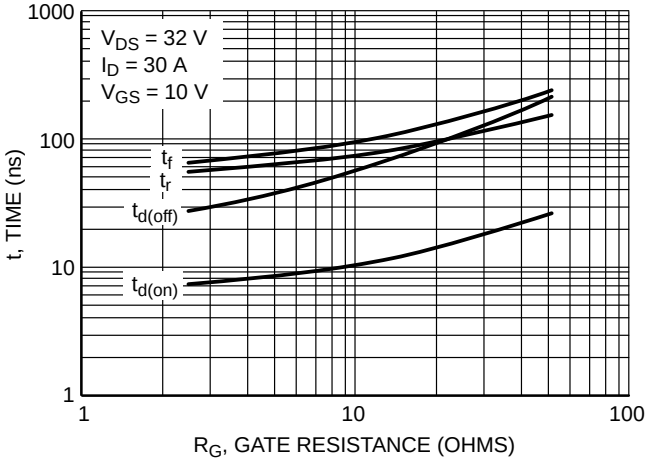


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

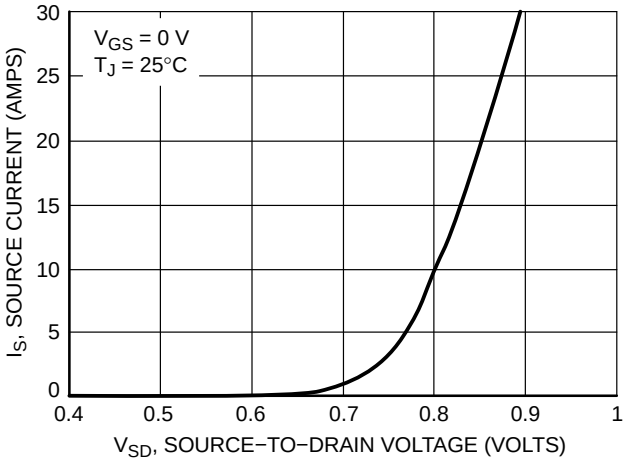


Figure 10. Diode Forward Voltage vs. Current

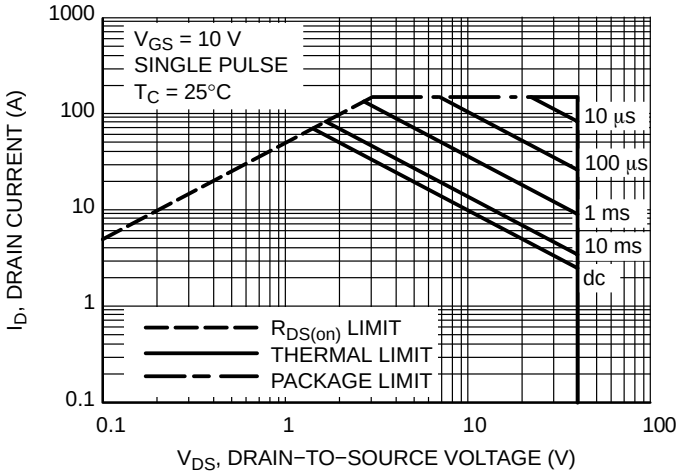


Figure 11. Maximum Rated Forward Biased Safe Operating Area

TYPICAL PERFORMANCE CURVES

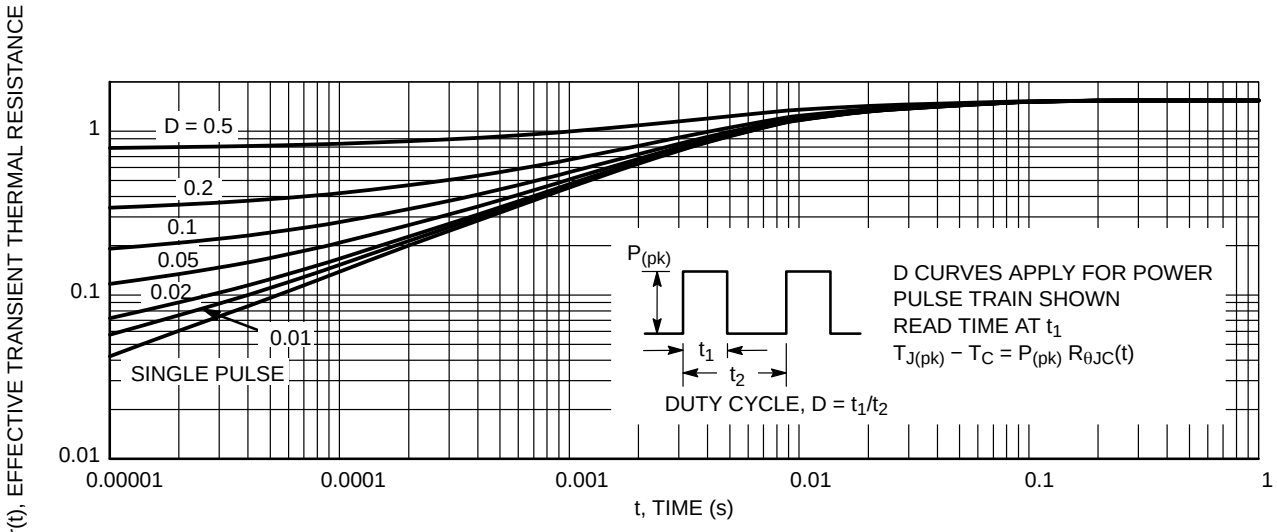
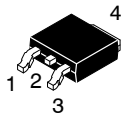


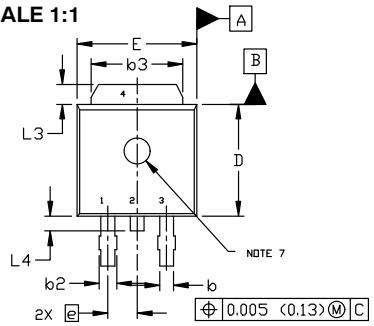
Figure 12. Thermal Response



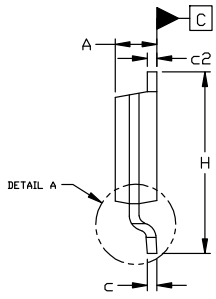
DPAK (SINGLE GAUGE)
CASE 369C
ISSUE G

DATE 31 MAY 2023

SCALE 1:1



TOP VIEW

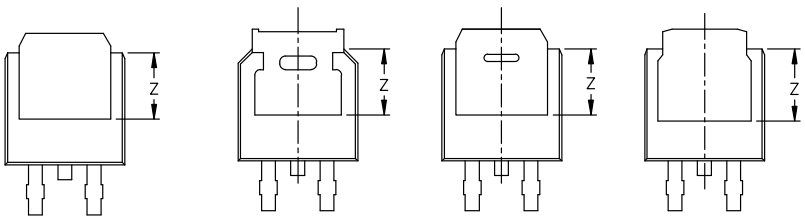


SIDE VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

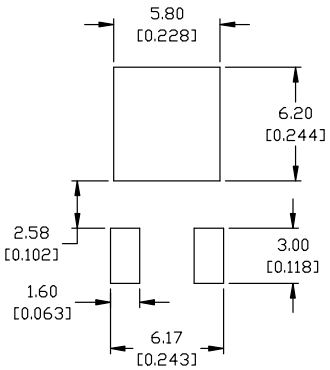
DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114 REF		2.90 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	----	0.040	---	1.01
Z	0.155	----	3.93	---



BOTTOM VIEW

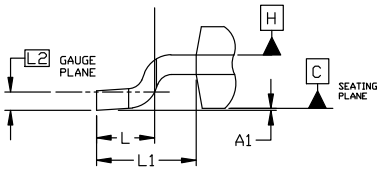
BOTTOM VIEW

ALTERNATE CONSTRUCTIONS



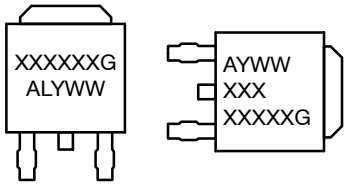
RECOMMENDED MOUNTING FOOTPRINT*

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.



DETAIL A
ROTATED 90° CW

GENERIC MARKING DIAGRAM*



IC **Discrete**

XXXXXX = Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE

STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2

STYLE 7:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 8:
PIN 1. N/C
2. CATHODE
3. ANODE
4. CATHODE

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. RESISTOR ADJUST
4. CATHODE

STYLE 10:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

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